

# East Search History (6pp) (5/30/04) *[Signature]*

L-Number	Hits	Search Text	DB	Time stamp
-	5	039404.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 15:01
-	4	039484.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/07 12:04
-	28	method near4 circuit adj simulation.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/07 12:08
-	0	apparatus near6 computer adj simulation near6 circuit.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/07 12:09
-	162	computer adj system near6 simulation.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/07 12:10
-	8	(US-20030154064-\$ or US-20030154065-\$ or US-20030154447-\$ or US-20030154453-\$ or US-20030154454-\$ or US-20030163277-\$ or US-20030163510-\$ or US-20030164239-\$).did.	US-PGPUB	2003/09/07 12:42
-	0	simulating.clm and apparatus.clm. and design.clm.	USPAT; US-PGPUB	2003/09/07 12:43
-	840	simulating near6 circuit.clm.	USPAT; US-PGPUB	2003/09/07 12:44
-	7	(US-20030154453-\$ or US-20030154454-\$ or US-20030163277-\$ or US-20030163510-\$ or US-20030154447-\$ or US-20030154065-\$ or US-20030154064-\$).did.	US-PGPUB	2004/05/19 11:21
-	1136	((703/13) or (703/14)).CCLS:	USPAT; US-PGPUB	2004/05/19 13:54
-	42	((((703/13) or (703/14)).CCLS.) and method near6 capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 14:16
-	0	((((703/13) or (703/14)).CCLS.) and method near6 capacitance and simulat\$3 near6 design adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 14:21
-	0	method near6 capacitance near6 simulat\$3 and simul\$3 near6 design adj structure and parasitic adj capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 15:16
-	0	method near6 capacitance near6 simulat\$3 and simul\$3 near6 design adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 15:16
-	1814	circuit near3 simulat\$3.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 15:16
-	95	circuit near3 simulat\$3.clm. and method near6 (capacitance capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 15:35

34	circuit near3 simulat\$3.clm. and method near6 (capacitance capacitor) and design near6 simulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 17:26
15	gallia.in. near6 james.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 17:29
5	gallia.in. near6 james.in. and design\$3 and capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 17:31
19	(design\$3 determin\$3) near3 capacitance near20 (circuit near2 simulat\$3).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 17:33
7	(design\$3 determin\$3) near3 capacitance near20 (circuit near2 simulat\$3).ti,ab,clm. and parasitic.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 10:38
1137	((703/13) or (703/14)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 10:38
58	((703/13) or (703/14)).CCLS.) and circuit adj simulati\$2 and design and capacitance and parasitic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 10:51
0	((703/13) or (703/14)).CCLS.) and circuit adj simulati\$2 and design adj structure and test adj structure and capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 10:52
0	((703/13) or (703/14)).CCLS.) and circuit adj simulati\$2 and design adj structure and test adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 10:52
158	((703/13) or (703/14)).CCLS.) and circuit adj simulati\$2 and design and test	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 10:52
8	((703/13) or (703/14)).CCLS.) and circuit adj simulati\$2 and design and test and capacitance and parasitic adj capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 11:10
4	((703/13) or (703/14)).CCLS.) and circuit adj simulati\$2 and design and test and capacitance and (wire interconnect) adj capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 11:18
0	estimat\$3 near2 parasitic adj capacitance near8 test	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 11:19
37	estimat\$3 near2 parasitic adj capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 11:19

1	estimat\$3 near2 parasitic adj capacitance and test adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 11:20
0	estimat\$3 near2 parasitic adj capacitance and test adj (device transistor capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 11:22
12	estimat\$3 near2 parasitic adj capacitance and simulation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 14:10
2	("6243653").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 15:35
6	extraction near4 parasitic adj capacitance.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 15:36
4	extraction near4 parasitic adj capacitance.ti,ab,clm. and circuit near2 simulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 15:36
0	6243653.ph. and physical\$2 near3 test\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:40
0	6243653.pn. and test\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:40
0	((("6243653").PN.) and physical\$2 and test\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:41
0	((("6243653").PN.) and test\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:41
2	("6243653").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:42
0	physical\$2 near2 test\$3 and extract\$3 near3 parasitic adj capacitance and simulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:43
1	physical\$2 near2 test\$3 and extract\$3 near3 parasitic adj capacitance and simulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:53
2	("5706206").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 11:10

	6	capacitance near3 test\$3 and capacitance near3 design\$3 and parasitic adj capacitance near4 test\$3 near6 design\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 11:12
	6	capacitance near3 (physical test\$3) and capacitance near3 (simulat\$3 design\$3 ) and parasitic adj capacitance near4 test\$3 near6 design\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 11:13
	45	capacitance near3 (physical test\$3) and capacitance near3 (simulat\$3 design\$3 ) and parasitic adj capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 11:13
	56	(extracting extraction) near4 (parasitic adj capacitance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 19:39
	5	(extracting extraction) near4 (parasitic adj capacitance) and subtract\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 19:48
	2	(extracting extraction) near4 (parasitic adj capacitance) and subtract\$3 and sum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 19:56
	5	(extracting extraction) near4 (parasitic adj capacitance) and subtract\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 19:56
	6	raphael and parasitic adj capacitance and three adj dimensional	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/25 14:34
	126	cmos and gate adj contact and parasitic adj capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/25 14:35
	84	width near2 gate and parasitic adj capacitance and (extracting extraction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 10:42
	2	width near2 gate and parasitic adj capacitance near3 (extracting extraction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:57
	0	raphael.ti,ab,clm. and boundary adj conditions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:57
	3	raphael and boundary adj conditions and parasitic adj capacitance.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:57
	2	overlap near3 gate and parasitic adj capacitance and raphael	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:17

-	3473	capacitance near3 drain near4 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 16:40
-	108	capacitance near3 drain near4 source and parasitic adj capacitance and simulation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 16:41
-	102	capacitance near3 drain near3 source and parasitic adj capacitance and simulation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 17:28
-	1	calibration adj structure and parasitic adj capacitance and test adj structure and simulation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 17:29
-	2	calibration and parasitic adj capacitance and test adj structure and simulation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 17:31
-	2	calibrati\$2 and parasitic adj capacitance and test adj structure and simulation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 17:31
-	2	6449754.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 09:12
-	19722	apparatus near3 simulating near3 integrated circuit near3 operation.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:18
-	0	apparatus near3 simulating near3 integrated adj circuit near3 operation.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:18
-	0	apparatus near6 simulating near6 integrated adj circuit near6 operation.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:22
-	0	apparatus near6 simulating near6 integrated adj circuit near6 operation.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:23
-	1	apparatus near6 simulati\$2 near6 integrated adj circuit near6 operation.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:24
-	4964	apparatus near6 simulati\$2.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:24
-	4087	apparatus near3 simulati\$2.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:25

-	383	apparatus near3 simulati\$2 near6 (semiconductor integrated circuit).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:26
-	4	039484.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 19:16
-	2	("6169302").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 18:06
-	62	apparatus near3 simulating near3 circuit.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 18:06
-	7	apparatus near3 simulating near3 circuit.ti,ab,clm. and computer.ti,ab,clm. and processor.ti,ab,clm. and memory.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 18:07